TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE (π-MOSⅥ)

TPC8004

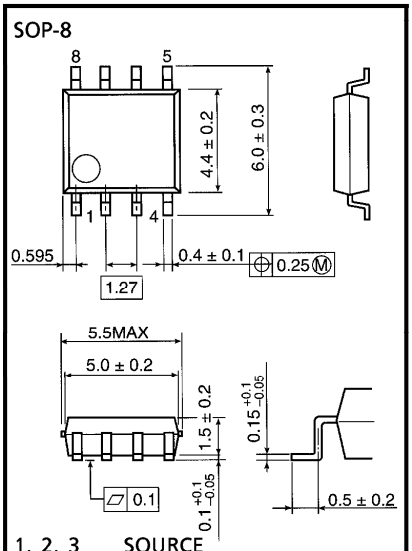
LITHIUM ION BATTERY APPLICATIONS

NOTE BOOK PC, PORTABLE EQUIPMENTS APPLICATIONS

INDUSTRIAL APPLICATIONS

- Low Drain-Source ON Resistance : $R_{DS\,(ON)}$ = 37 mΩ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}|$ = 6 S (Typ.)
- Low Leakage Current : I_{DSS} = 10 μA (Max.) (V_{DS} = 30 V)
- Enhancement-Model : V_{th} = 0.8~2.0 V (V_{DS} = 10 V, I_D = 1 mA)

Unit in mm



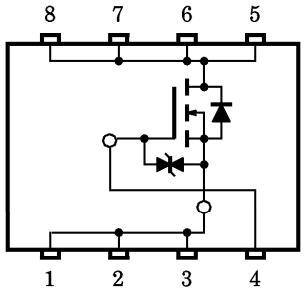
JEDEC	—
EIAJ	—
TOSHIBA	2-6J1A

Weight : 0.08g

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain-Source Voltage		V_{DSS}	30	V
Drain-Gate Voltage (R_{GS} = 20 kΩ)		V_{DGR}	30	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current	DC	I_D	5	A
	Pulse	I_{DP}	20	A
Drain Power Dissipation (Ta = 25°C)		P_D	2.4	W
Single Pulse Avalanche Energy*		E_{AS}	32.5	mJ
Avalanche Current		I_{AR}	5	A
Repetitive Avalanche Energy**		E_{AR}	0.24	mJ
Channel Temperature		T_{ch}	150	°C
Storage Temperature Range		T_{stg}	−55~150	°C

CIRCUIT CONFIGURATION



THERMAL CHARACTERISTICS

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient	$R_{th\,(ch\text{-}a)}$	52.1	°C / W

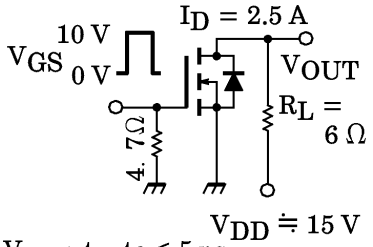
Note ;

* V_{DD} = 24 V, T_{ch} = 25°C, L = 1.0 mH, I_{AR} = 5.0 A, R_G = 25 Ω

** Repetitive rating ; Pulse Width Limited by Max. Junction temperature.

This transistor is an electrostatic sensitive device. Please handle with caution.

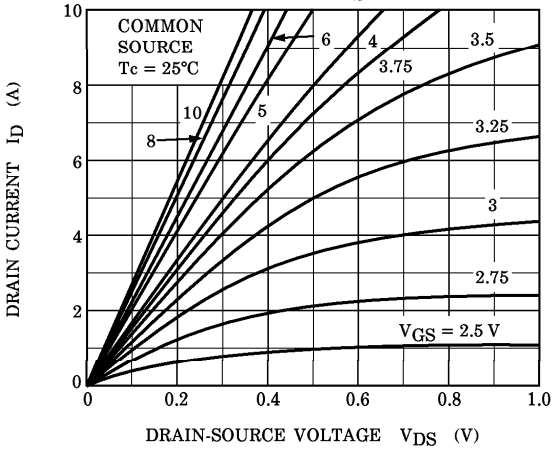
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current		I_{GSS}	V_{GS} = ±16 V, V_{DS} = 0 V	—	—	±10	μA
Drain Cut-Off Current		I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V	—	—	10	μA
Drain-Source Breakdown Voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	30	—	—	V
Gate Threshold Voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	0.8	—	2.0	V
Drain-Source ON Resistance		$R_{DS\ (ON)}$	V_{GS} = 4 V, I_D = 2.5 A	—	58	80	mΩ
			V_{GS} = 10 V, I_D = 2.5 A	—	37	50	
Forward Transfer Admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 2.5 A	3	6	—	S
Input Capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	475	—	pF
Reverse Transfer Capacitance		C_{rss}		—	85	—	
Output Capacitance		C_{oss}		—	270	—	
Switching Time	Rise Time	t_r	 V_{IN} : t_r, t_f < 5 ns Duty ≦ 1%, t_w = 10 μs	—	10	—	ns
	Turn-On Time	t_{on}		—	16	—	
	Fall Time	t_f		—	13	—	
	Turn-Off Time	t_{off}		—	70	—	
Total Gate Charge (Gate-Source Plus Gate-Drain)		Q_g	V_{DD} ≒ 24 V, V_{GS} = 10 V, I_D = 5 A	—	16	—	nC
Gate-Source Charge		Q_{gs}		—	11	—	
Gate-Drain ("Miller") Charge		Q_{gd}		—	5	—	

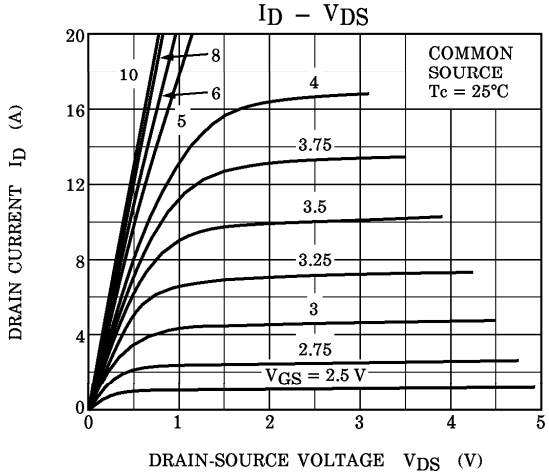
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Continuous Drain Reverse Current	I_{DR}	—	—	—	5	A
Pulse Drain Reverse Current	I_{DRP}	—	—	—	20	A
Diode Forward Voltage	V_{DSF}	I_{DR} = 5 A, V_{GS} = 0 V	—	—	−1.2	V

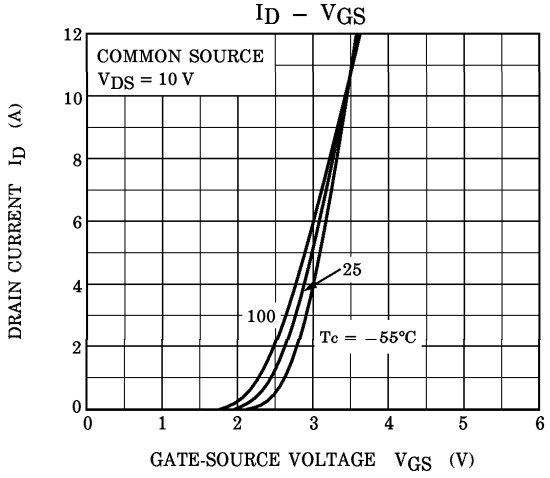
$I_D - V_{DS}$



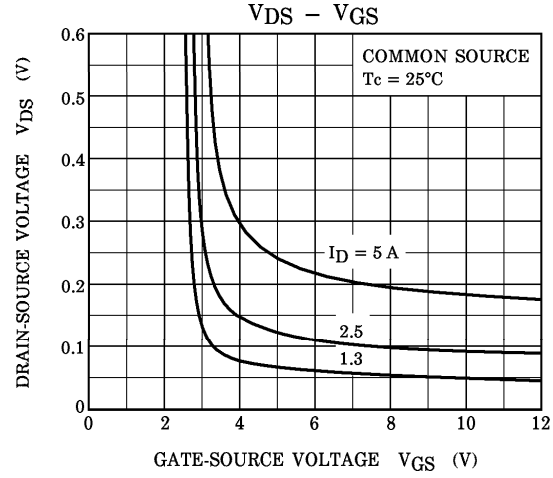
$I_D - V_{DS}$



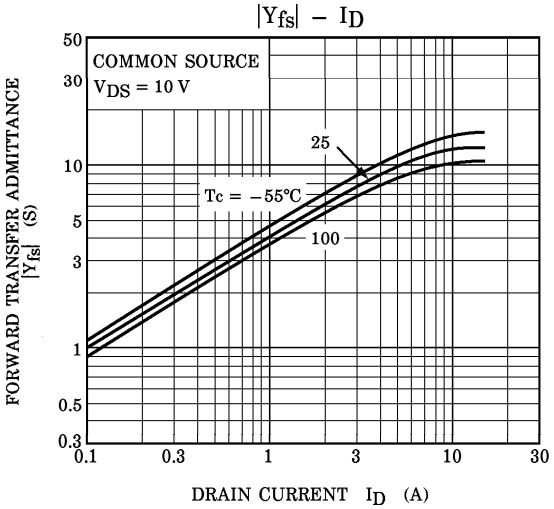
$I_D - V_{GS}$



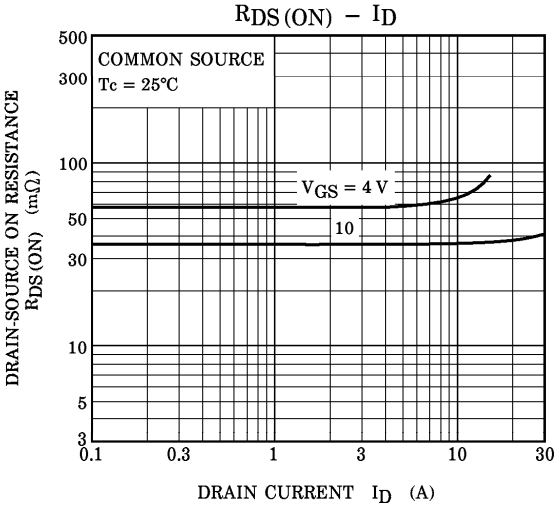
$V_{DS} - V_{GS}$



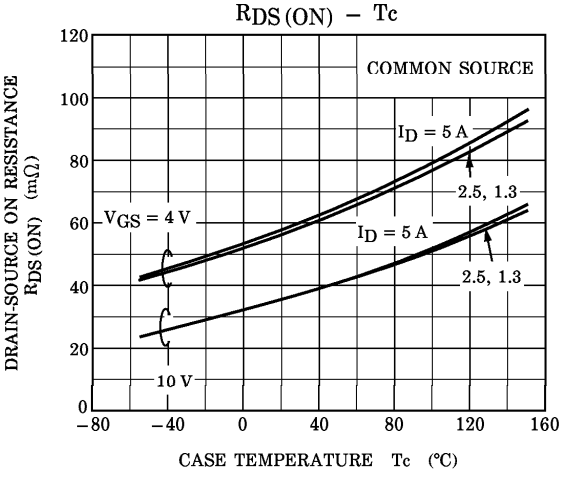
$|Y_{fs}| - I_D$



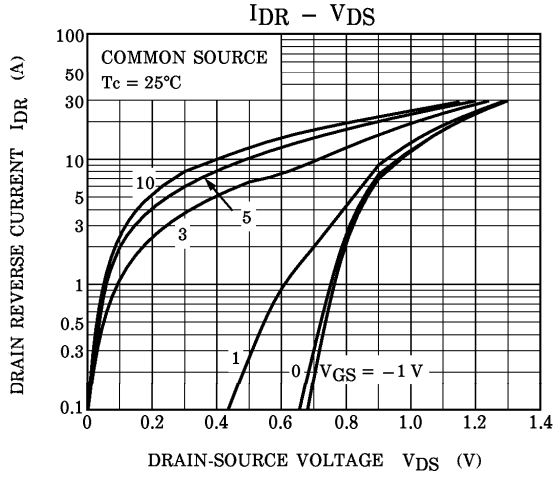
$R_{DS\,(ON)} - I_D$



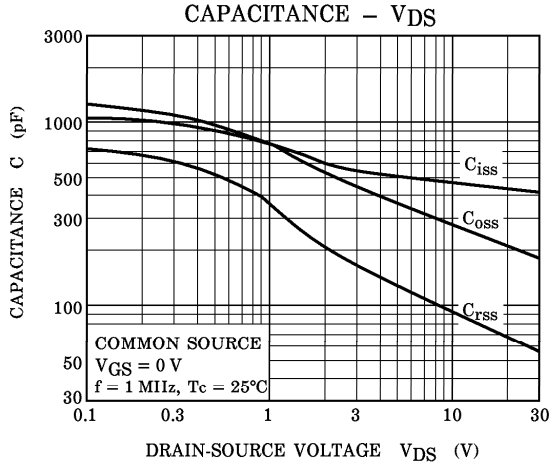
$R_{DS\,(ON)}$ – Tc



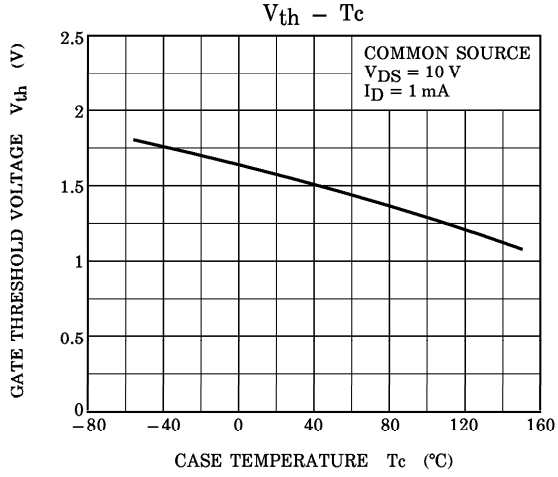
I_{DR} – V_{DS}



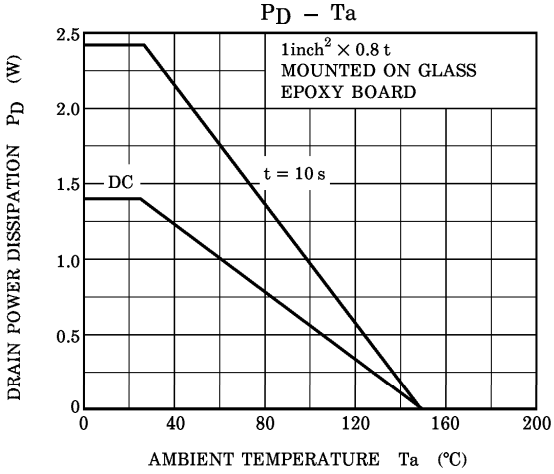
CAPACITANCE – V_{DS}



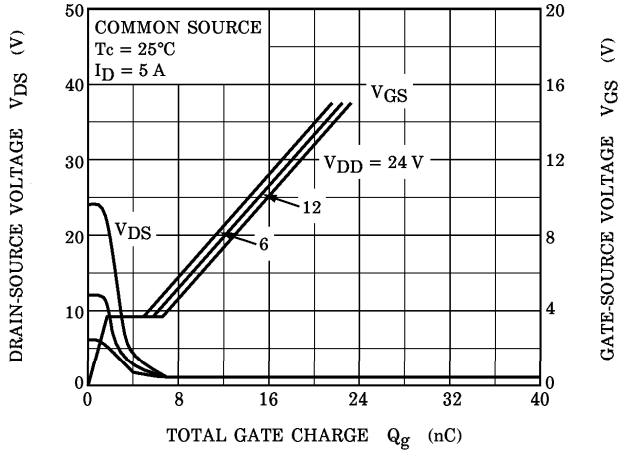
V_{th} – Tc



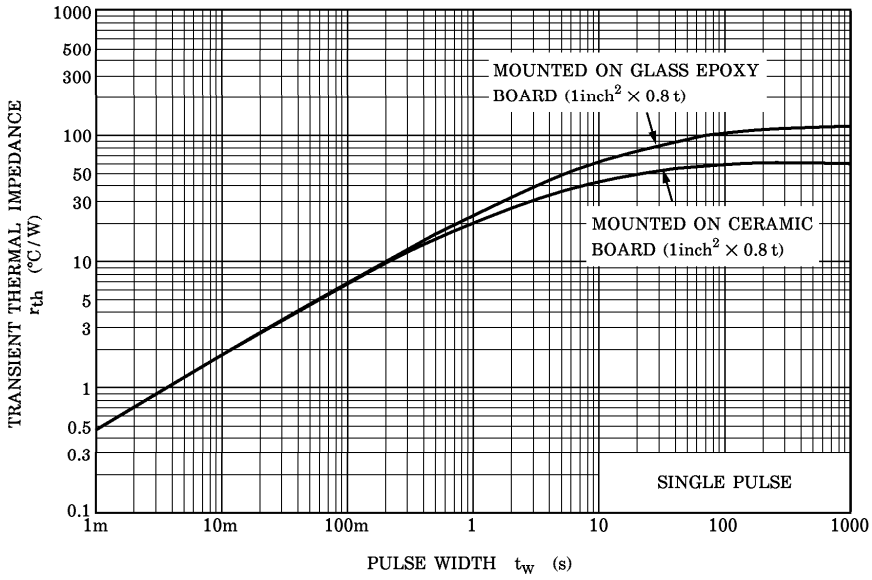
P_D – Ta



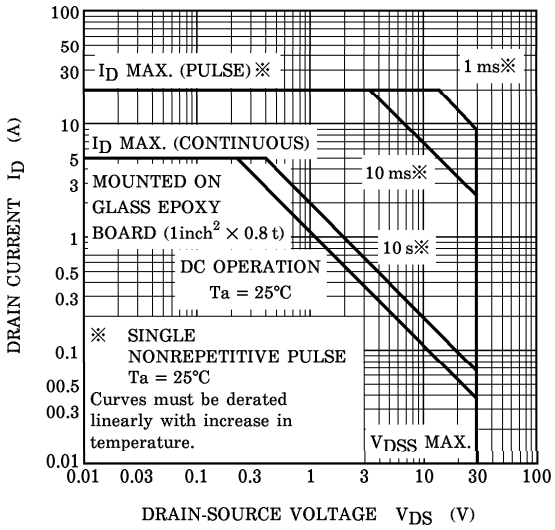
DYNAMIC INPUT / OUTPUT CHARACTERISTICS



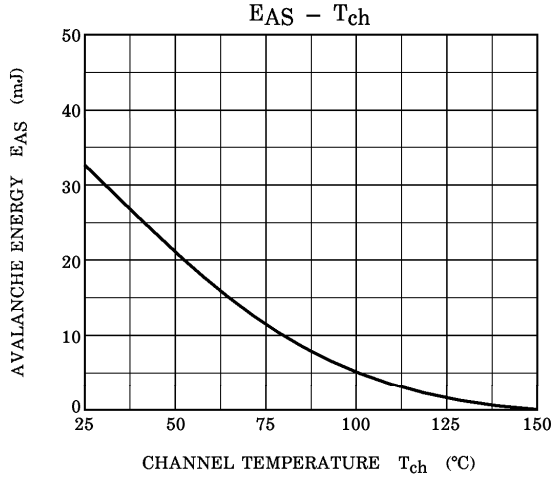
r_{th} – t_w

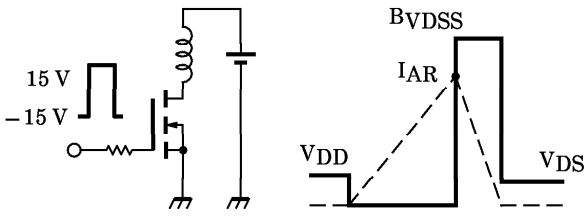


SAFE OPERATING AREA



E_{AS} – T_{ch}





TEST CIRCUIT WAVE FORM

Peak I_{AR} = 5 A, R_G = 25 Ω
V_{DD} = 24 V, L = 1.0 mH

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$